

AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A diamond n-type semiconductor comprising a first diamond semiconductor which has n-type conduction and in which a distortion or defect is artificially formed,

wherein said first diamond semiconductor contains at least one kind donor element of  $5 \times 10^{19} \text{ cm}^{-3}$  or more in total and an impurity element other than the donor element, the contained amount of the impurity element being lower than the total contained amount of the donor element, [[and]]

whereby said first diamond semiconductor has an n-type dopant concentration adjusted by vapor-phase growth such that an electron concentration of said first diamond semiconductor exhibits a negative correlation with temperature, in a temperature range having a width of  $100^{\circ}\text{C}$  or more and included within a temperature region from  $0^{\circ}\text{C}$  to  $300^{\circ}\text{C}$ , and

wherein the impurity element is Si locally existing in said first diamond semiconductor as a material for restraining the deterioration of diamond crystallinity caused by the doping of the donor element.

2. (Previously Presented) A diamond n-type semiconductor according to claim 1, wherein said first diamond semiconductor has a Hall coefficient exhibiting a positive correlation with temperature, in the temperature range.

3. (Previously Presented) A diamond n-type semiconductor according to claim 1, wherein the temperature range, included within the temperature region from  $0^{\circ}\text{C}$  to  $300^{\circ}\text{C}$ , has a width of over  $200^{\circ}\text{C}$  or more.

4. (Previously Presented) A diamond n-type semiconductor according to claim 1, wherein said first diamond semiconductor has a resistivity of 500  $\Omega\text{cm}$  or less at a temperature within the temperature region from 0°C to 300°C.

5. (Previously Presented) A diamond n-type semiconductor according to claim 1, wherein the electron concentration of said first diamond semiconductor is always  $10^{16} \text{ cm}^{-3}$  or more in the temperature region from 0°C to 300°C.

6. (Cancelled)

7. (Previously Presented) A diamond n-type semiconductor according to claim 1, wherein said first diamond semiconductor contains at least P (phosphorus) as the donor element.

8. (Previously Presented) A diamond n-type semiconductor according to claim 1, wherein said first diamond semiconductor contains at least S (sulfur) as the donor element.

9. (Cancelled)

10. (Currently Amended) A diamond n-type semiconductor according to claim 1, wherein ~~said first diamond semiconductor contains~~ the contained amount of Si [[of]] is  $1 \times 10^{17} \text{ cm}^{-3}$  or more as the impurity element.

11. (Previously Presented) A diamond n-type semiconductor according to claim 1, wherein said first diamond semiconductor is monocrystal diamond.

12. (Previously Presented) A diamond n-type semiconductor according to claim 1, further comprising a second diamond semiconductor provided adjacent to said first diamond semiconductor and turned out to be n-type,

wherein said second diamond semiconductor has an electron concentration not exhibiting a negative correlation with temperature and a Hall coefficient not exhibiting a positive correlation with temperature, in the temperature range.

13. (Previously Presented) A semiconductor device at least partly employing a diamond n-type semiconductor according to claim 1.

14. (Previously Presented) An electron emitting device having the diamond n-type semiconductor according to claim 1 employed in at least an electron emitting part thereof.

15. (Currently Amended) A method of manufacturing a diamond n-type semiconductor according to claim 1, said method comprising the steps of:

preparing a diamond substrate; and

epitaxially growing a diamond semiconductor on said diamond substrate by vapor phase growth while artificially introducing an impurity element other than a donor element to said diamond substrate, whereby said diamond semiconductor has n-type conduction and has a distortion or defect which is artificially formed therein,

wherein the Si is artificially introduced as the impurity element to said diamond substrate.

16. (Cancelled)